SRS-2010 Spread resistance for slanting polished sample of semiconductor by tow kinematically-mounted probe contacting.

Selling Points

Resitivity map along with depth direction, thickness of epitaxial, depth of PN junctin and carier density profiles

Details

Applications

Semiconductor materials, Solar-cell materials (Silicon, Polysilicon, SiC etc)

Sample sizes

Please contact us in details

Measuring range

1~10E+9 Ω[Spread restance]
Carrier density range:2E+13 ~ 5E+19 cm2 [N-type silicon]
2E+14 ~ 7E+19 cm2 [P-type silicon]